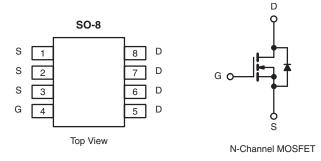




N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A) ^a	Q _g (Typ.)			
30	0.0195 at V _{GS} = 10 V	8	9.2 nC			
30	0.023 at V _{GS} = 4.5 V	8	9.2110			



FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- Compliant to RoHS Directive 2002/95/EC

ROHS COMPLIANT HALOGEN FREE

APPLICATIONS

- · Notebook Load Switch
- Low Current dc-to-dc

ABSOLUTE MAXIMUM RATINGS T	$_{A}$ = 25 °C, unless other	erwise noted			
Parameter			Limit	Unit	
Drain-Source Voltage			30	V	
Gate-Source Voltage			± 20	V	
	T _C = 25 °C		8 ^a	A	
Continuous Drain Current (T _{.I} = 150 °C)	T _C = 70 °C] ,	8 ^a		
Continuous Diain Current (1 j = 150 °C)	T _A = 25 °C	I _D	7.5 ^{b,c}		
	T _A = 70 °C		5.9 ^{b,c}		
Pulsed Drain Current	I _{DM}	30			
Continuous Course Drain Diade Current	T _C = 25 °C	,	2.7		
Continuous Source-Drain Diode Current	T _A = 25 °C	- I _S	1.7 ^{b,c}		
	T _C = 25 °C		4.1		
Maximum Dawar Dissination	T _C = 70 °C		2.6	w	
Maximum Power Dissipation	T _A = 25 °C	- P _D	2 ^{b,c}		
	T _A = 70 °C		1.25 ^{b,c}		
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{b, d}	t ≤ 5 s	R _{thJA}	45	62.5	°C/W	
Maximum Junction-to-Foot	Steady State	R _{th,IF}	25	30]	

Notes

- a. Package Limited.
- b. Surface mounted on 1" x 1" FR4 board.
- c. t = 5 s
- d. Maximum under Steady State conditions is 110 $^{\circ}$ C/W.



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V, } I_D = 250 \mu\text{A}$	30			V	
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I _D = 250 μA		33			
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I _D = 250 μA		- 6.2		mV/°C	
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1		3	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
7 0 1 1/1 5 1 0 1	1	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$			1		
Zero Gate Voltage Drain Current	IDSS	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 \text{ °C}$			10	μΑ	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	20			Α	
	_	$V_{GS} = 10 \text{ V}, I_D = 5 \text{ A}$		0.016	0.0195		
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 4 \text{ A}$		0.019	0.023	Ω	
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 10 \text{ V}, I_D = 5 \text{ A}$		24		S	
Dynamic ^b						<u> </u>	
Input Capacitance	C _{iss}			1295			
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		170		pF	
Reverse Transfer Capacitance	C _{rss}			72			
	1	$V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 5 \text{ A}$		21.8	33		
Total Gate Charge	Q_g			9.2	14		
Gate-Source Charge	Q_{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 5 \text{ A}$		3.8		nC	
Gate-Drain Charge	Q _{gd}			2.5			
Gate Resistance	R _q	f = 1 MHz		2.4		Ω	
Turn-On Delay Time	t _{d(on)}			21	40		
Rise Time	t _r	V_{DD} = 15 V, R_L = 3 Ω		14	25		
Turn-Off DelayTime	t _{d(off)}	$I_D \cong 5 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_q = 1 \Omega$		20	40		
Fall Time	t _f	· ·		9	18		
Turn-On Delay Time	t _{d(on)}			10	20	ns	
Rise Time	t _r	V_{DD} = 15 V, R_L = 3 Ω		8	16		
Turn-Off DelayTime	t _{d(off)}	$I_D \cong 5 \text{ A}, V_{GEN} = 10 \text{ V}, R_q = 1 \Omega$		21	35		
Fall Time	t _f	Ç		8	16		
Drain-Source Body Diode Characteris	tics					L	
Continous Source-Drain Diode Current	I _S	T _C = 25 °C			2.7		
Pulse Diode Forward Current	I _{SM}	-	1		30	Α	
Body Diode Voltage	V _{SD}	I _S = 1.7 A, V _{GS} = 0 V	1	0.77	1.2	V	
Body Diode Reverse Recovery Time	t _{rr}		1	21	40	ns	
Body Diode Reverse Recovery Charge	Q _{rr}	L 0.0 dl/dt 100 0/1/2 T 05 00		15	30	nC	
Reverse Recovery Fall Time	t _a	$I_F = 3 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 ^{\circ}\text{C}$	Ü	13			
Reverse Recovery Rise Time		t _b		8		ns	

Notes:

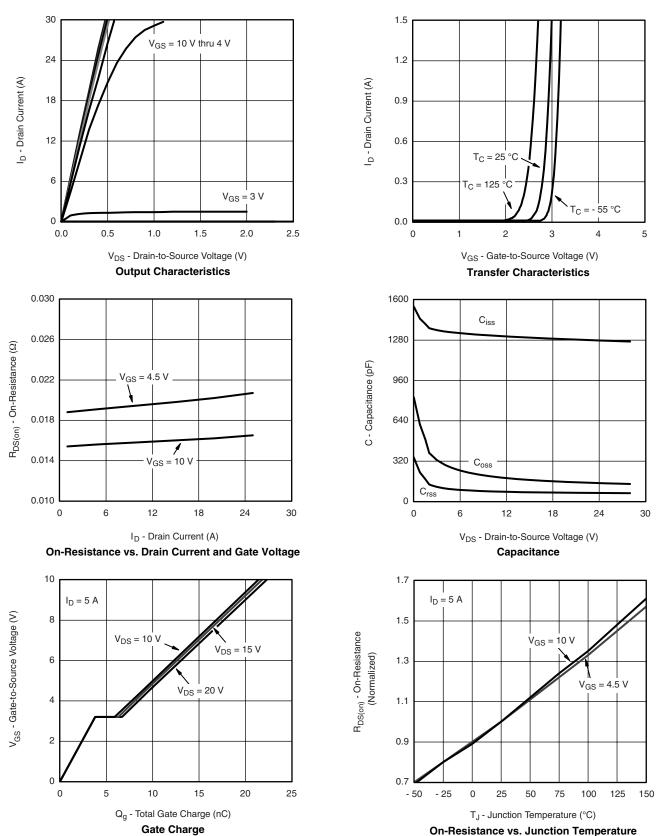
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$

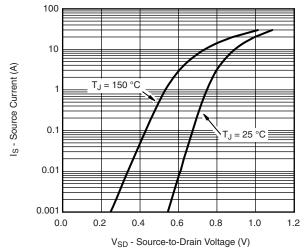
b. Guaranteed by design, not subject to production testing.



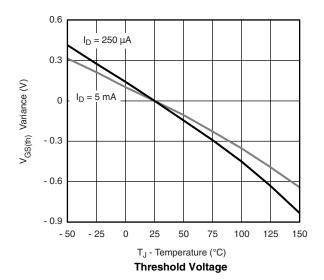
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

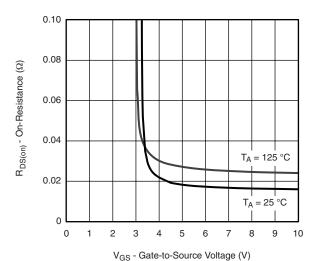


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

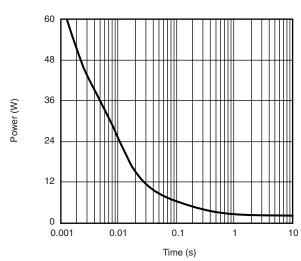


Source-Drain Diode Forward Voltage

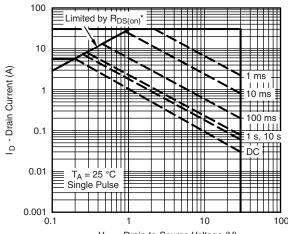




On-Resistance vs. Gate-to-Source Temperature



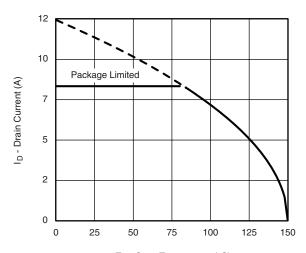
Single Pulse Power, Junction-to-Ambient



 $V_{DS} \mbox{ - Drain-to-Source Voltage (V)} $$ ^*V_{GS} > minimum V_{GS} \mbox{ at which } R_{DS(on)} \mbox{ is specified} $$$

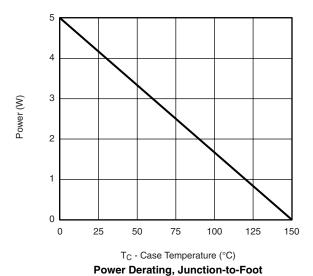
Safe Operating Area, Junction-to-Ambient

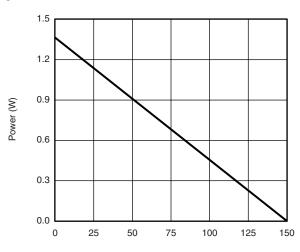
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



 $T_{\mbox{\scriptsize C}}$ - Case Temperature (°C)

Current Derating*

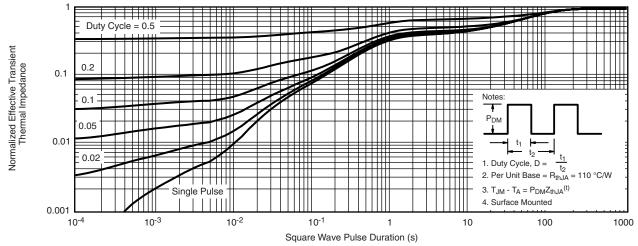




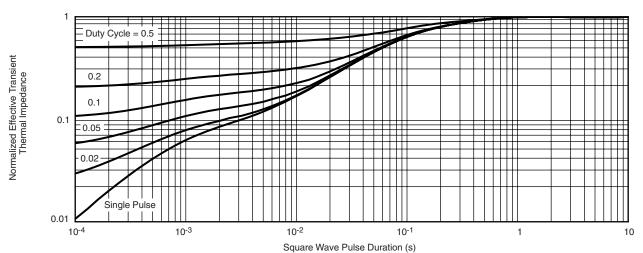
T_A - Ambient Temperature (°C) **Power Derating, Junction-to-Ambient**

^{*} The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



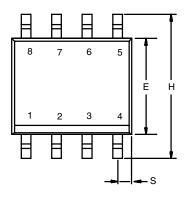
Normalized Thermal Transient Impedance, Junction-to-Ambient

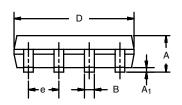


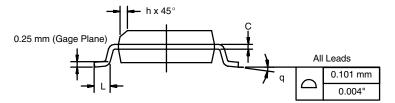
Normalized Thermal Transient Impedance, Junction-to-Foot



SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012





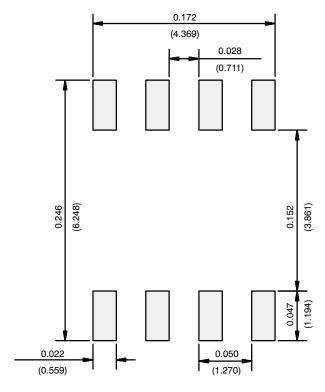


	MILLIM	IETERS	INCHES			
DIM	Min	Max	Min	Max		
Α	1.35	1.75	0.053	0.069		
A ₁	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
Е	3.80	4.00	0.150	0.157		
е	1.27	1.27 BSC 0		50 BSC		
Н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
ECN: C-06527-Rev. I, 11-Sep-06						

DWG: 5498



RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index



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